

WEST Search History

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DATE: Tuesday, March 28, 2006

| Hide? | Set Name | Query | Hit Count |
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| | <i>DB=PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR</i> | | |
| <input type="checkbox"/> | L37 | 6730939 | 3 |
| <input type="checkbox"/> | L36 | 4608117 | 38 |
| <input type="checkbox"/> | L35 | L34 and l32 | 59 |
| <input type="checkbox"/> | L34 | gate or wire or pixel or drain | 3365571 |
| <input type="checkbox"/> | L33 | L32 and l1 | 0 |
| <input type="checkbox"/> | L32 | L31 same l13 | 172 |
| <input type="checkbox"/> | L31 | l5 same l11 | 648 |
| | <i>DB=JPAB; PLUR=YES; OP=OR</i> | | |
| <input type="checkbox"/> | L30 | l29 and l28 | 0 |
| <input type="checkbox"/> | L29 | currentless | 9 |
| <input type="checkbox"/> | L28 | l17 | 12 |
| <input type="checkbox"/> | L27 | l16 | 0 |
| <input type="checkbox"/> | L26 | l16 and l17 and l18 | 0 |
| <input type="checkbox"/> | L25 | 57-043977.pn. | 0 |
| <input type="checkbox"/> | L24 | 57-43977 | 0 |
| <input type="checkbox"/> | L23 | 570043977 | 0 |
| <input type="checkbox"/> | L22 | 57043977.pn. | 0 |
| | <i>DB=PGPB,USPT,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR</i> | | |
| <input type="checkbox"/> | L21 | l20 and l11 | 4 |
| <input type="checkbox"/> | L20 | l13 and l19 | 8 |
| <input type="checkbox"/> | L19 | L18 and l17 and l16 | 29 |
| <input type="checkbox"/> | L18 | wolf.inv. | 22605 |
| <input type="checkbox"/> | L17 | giesecke.inv. | 278 |
| <input type="checkbox"/> | L16 | ebneth.inv. | 125 |
| <input type="checkbox"/> | L15 | L14 and l1 | 11 |
| <input type="checkbox"/> | L14 | L13 same l5 | 3123 |
| <input type="checkbox"/> | L13 | light or irradiat\$5 | 3268036 |
| <input type="checkbox"/> | L12 | L11 and l10 | 6 |
| <input type="checkbox"/> | L11 | pattern | 1707313 |
| <input type="checkbox"/> | L10 | L9 and l6 | 38 |
| <input type="checkbox"/> | L9 | palladium and dichloride | 9860 |

| | | | |
|--------------------------|----|----------------------------|---------|
| <input type="checkbox"/> | L8 | palladiaum and dichloride | 0 |
| <input type="checkbox"/> | L7 | palladium and dichlorideL6 | 0 |
| <input type="checkbox"/> | L6 | L5 and l1 | 981 |
| <input type="checkbox"/> | L5 | organometal\$5 | 58503 |
| <input type="checkbox"/> | L4 | L3 and l1 | 24799 |
| <input type="checkbox"/> | L3 | metal\$5 or organ\$5 | 5106626 |
| <input type="checkbox"/> | L2 | metal\$5 or organ\$5L1 | 4050784 |
| <input type="checkbox"/> | L1 | bayer.asn. | 63975 |

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L29: Entry 4 of 9

File: JPAB

Mar 10, 1998

PUB-NO: JP410070128A

DOCUMENT-IDENTIFIER: JP 10070128 A

TITLE: METHOD OF FORMATION OF PALLADIUM CONTACT BUMP ON SEMICONDUCTOR CIRCUIT CARRIER

PUBN-DATE: March 10, 1998

INVENTOR-INFORMATION:

NAME

COUNTRY

MEYER, HEINRICH DR DR

MAHLKOW, HARTMUT

ASCHENBRENNER, ROLF

ASSIGNEE-INFORMATION:

NAME

COUNTRY

ATOTECH DEUTSCHE GMBH

FRAUNHOFER GES

APPL-NO: JP09196019

APPL-DATE: July 22, 1997

INT-CL (IPC): H01 L 21/321

ABSTRACT:

PROBLEM TO BE SOLVED: To deposit a uniformly thick palladium contact bump on a conductor by a method wherein, after an aluminum conductor has been treated by an activating solution containing acidic palladium ions, a neutral currentless palladium deposition bath, containing formic acid or formic acid delivative, palladium ions and a nitrogen containing a complexing agent, is used.

SOLUTION: A metal intermediate layer 5 is selectively deposited on the surface of a cleaned aluminum conductive layer 1 using a zing ion aqueous solution. Also, the surface of a silicon base 4, which is not covered by an aluminum bonded pad 1, is covered by a passivated layer 3. Subsequently, a thin palladium layer 6 is formed on the aluminum bonded pad 1. After the palladium layer 6 has been activated by a strong acidic solution containing perchloric acid potassium (oxidizing agent) and sulfuric acid palladium, a contact bump 7 is deposited on the palladium layer using a non-current palladium bath (pH value of 4 to 7) containing ehtylenediamine (complexing agent) and sodium formate (reducing agent). The temperature of above-mentioned bath is about 70°C, and the deposition thickness is corresponded to treatment time.

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L35: Entry 57 of 59

File: DWPI

Aug 11, 2005

DERWENT-ACC-NO: 2005-566813

DERWENT-WEEK: 200558

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TITLE: Precipitation of metal and/or metal oxide for pattern formation, involves irradiating film containing organometallic compound and/or complex with energy beam, and decomposing organic component in film at irradiated region

INVENTOR: HIYAMA, H; SUMIYA, M ; YOKOTA, H

PATENT-ASSIGNEE: EBARA CORP (EBAR)

PRIORITY-DATA: 2004JP-0020856 (January 29, 2004)

Search Selected

Search ALL

Clear

PATENT-FAMILY:

| PUB-NO | PUB-DATE | LANGUAGE | PAGES | MAIN-IPC |
|--|-----------------|----------|-------|------------|
| <input type="checkbox"/> JP 2005213567 A | August 11, 2005 | | 017 | C23C018/14 |

APPLICATION-DATA:

| PUB-NO | APPL-DATE | APPL-NO | DESCRIPTOR |
|---------------|------------------|----------------|------------|
| JP2005213567A | January 29, 2004 | 2004JP-0020856 | |

INT-CL (IPC): B82 B 3/00; C01 B 31/02; C23 C 18/14; H01 J 1/304; H01 J 9/02

ABSTRACTED-PUB-NO: JP2005213567A

BASIC-ABSTRACT:

NOVELTY - A film containing an organometallic compound and/or an organometallic complex, is formed and irradiated with an energy beam. The organic component contained in the film positioned at the irradiated region is decomposed, and a metal and/or a metal oxide are precipitated.

DETAILED DESCRIPTION - INDEPENDENT CLAIMS are included for the following:

- (1) particles of metal and/or metal oxide produced by the process;
- (2) film of metal and/or metal oxide;
- (3) wire of metal and/or metal oxide;
- (4) metallic mold of metal and/or metal oxide;
- (5) semiconductor device;

(6) manufacture of carbon fiber or carbon tube, which involves forming particles of metal and/or metal oxide on a substrate, contacting the substrate with hydrocarbon gas and/or carbon-monoxide gas, heating the substrate, and forming carbon fiber or carbon tube on the particles;

(7) manufacture of optical waveguide, which involves forming a pattern of particles of metal and/or metal oxide on a substrate at equal spacing;

(8) manufacture of single electron transistor, which involves using the particles of metal and/or metal oxide as a conductor island;

(9) manufacture of field emitter, which involves using the particles as an emitter tip;

(10) optical waveguide;

(11) single electron transistor;

(12) field emitter; and

(13) pattern forming apparatus (10) of metal and/or metal oxide, equipped with a unit (14) for forming a film of organometallic compound and/or complex, and a unit (18) for irradiating with an energy beam.

USE - For precipitating metal and/or metal oxide in form of particles, films, wires and metallic molds, used for pattern formation in manufacture of semiconductor device, carbon fiber or carbon tube, optical waveguide, single electron transistor, field emitter (all claimed), and other functional materials, such as electric, magnetic and light functional materials used for nano-size catalysts.

ADVANTAGE - The precipitation method enables easy and convenient pattern formation.

DESCRIPTION OF DRAWING(S) - The figure shows the pattern forming apparatus.
(Drawing includes non-English language text).

pattern forming apparatus 10

wafer delivery opening 12

film-forming unit 14

irradiation unit 18

washing-drying unit 20

ABSTRACTED-PUB-NO: JP2005213567A
EQUIVALENT-ABSTRACTS:

CHOSEN-DRAWING: Dwg.4/10

DERWENT-CLASS: E36 L03 Q68 U11 V05 X25

CPI-CODES: E05-B03; E05-D; E05-F02B; E05-L; E05-M01; E05-M02A; E05-M02C; E05-M03A; E05-M03B; E05-N02C; E05-N03B; E05-U03; E05-V03; E11-A; E31-N01; E31-P03; E34-C01; E35; L03-G02; L04-C06; L04-E01; N01-C02; N01-D02; N02-A01; N02-B01; N02-C01; N02-D01; N02-E01; N02-E03; N02-E04; N02-F; N03-B; N03-C01; N03-C03; N03-D01; N03-E;

N03-F; N03-G; N07-J;

EPI-CODES: U11-C05B4; U11-C05C6; V05-F05A7A; V05-F05A7C; V05-F05A7X; V05-F05E5;

V05-F08D1; X25-A09;

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